

FDS4501H

Complementary PowerTrench[®] Half-Bridge MOSFET

General Description

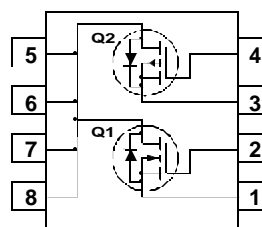
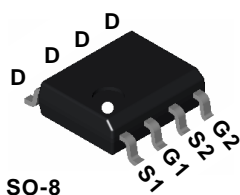
This complementary MOSFET half-bridge device is produced using Fairchild's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

Applications

- DC/DC converter
- Power management
- Load switch
- Battery protection

Features

- **Q1: N-Channel**
9.3A, 30V $R_{DS(on)} = 18\text{ m}\Omega @ V_{GS} = 10\text{V}$
 $R_{DS(on)} = 23\text{ m}\Omega @ V_{GS} = 4.5\text{V}$
- **Q2: P-Channel**
-5.6A, -20V $R_{DS(on)} = 46\text{ m}\Omega @ V_{GS} = -4.5\text{V}$
 $R_{DS(on)} = 63\text{ m}\Omega @ V_{GS} = -2.5\text{V}$



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Q1	Q2	Units
V _{DSS}	Drain-Source Voltage	30	-20	V
V _{GSS}	Gate-Source Voltage	±20	±8	V
I _b	Drain Current - Continuous (Note 1a)	9.3	-5.6	A
	- Pulsed	20	-20	
P _b	Power Dissipation for Single Operation (Note 1a)	2.5		W
	(Note 1b)	1.2		
	(Note 1c)	1		
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150		°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	25	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS4501H	FDS4501H	13"	12mm	2500 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_b = 250\ \mu\text{A}$ $V_{GS} = 0\text{ V}, I_b = -250\ \mu\text{A}$	Q1 Q2	30 -20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_b = 250\ \mu\text{A}$, Referenced to 25°C $I_b = -250\ \mu\text{A}$, Referenced to 25°C	Q1 Q2		24 -13		mV/ $^\circ\text{C}$
I_{BSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$	Q1 Q2			1 -1	μA
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ $V_{GS} = \pm 8\text{ V}, V_{DS} = 0\text{ V}$	Q1 Q2			± 100 ± 100	nA
On Characteristics (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_b = 250\ \mu\text{A}$ $V_{DS} = V_{GS}, I_b = -250\ \mu\text{A}$	Q1 Q2	1 -0.4	1.6 -0.7	3 -1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_b = 250\ \mu\text{A}$, Referenced to 25°C $I_b = -250\ \mu\text{A}$, Referenced to 25°C	Q1 Q2		-4 3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_b = 9.3\text{ A}$ $V_{GS} = 10\text{ V}, I_b = 9.3\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 4.5\text{ V}, I_b = 7.6\text{ A}$ $V_{GS} = -4.5\text{ V}, I_b = -5.6\text{ A}$ $V_{GS} = -4.5\text{ V}, I_b = -5.6\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = -2.5\text{ V}, I_b = -5.0\text{ A}$	Q1 Q2		14 21 17 36 49 47	18 29 23 46 80 63	m Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$ $V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	Q1 Q2	20 -20			A
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}, I_b = 9.3\text{ A}$ $V_{DS} = 5\text{ V}, I_b = -5.6\text{ A}$	Q1 Q2		28 16		S
Dynamic Characteristics							
C_{iss}	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	Q1 Q2		1958 1312		pF
C_{oss}	Output Capacitance		Q1 Q2		424 240		pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		182 106		pF

Electrical Characteristics (continued)

$T_A = 25^\circ\text{C}$ unless otherwise noted

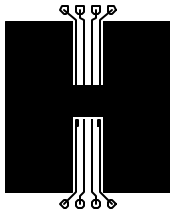
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Switching Characteristics (Note 2)							
$t_{d(on)}$	Turn-On Delay Time	Q1 $V_{DD} = 15\text{ V}, I_D = 1\text{ A},$	Q1		15	27	ns
			Q2		15	27	
t_r	Turn-On Rise Time	$V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$ Q1	Q1		5	10	ns
			Q2		15	27	
$t_{d(off)}$	Turn-Off Delay Time	$V_{DD} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$	Q1		38	61	ns
			Q2		40	64	
t_f	Turn-Off Fall Time		Q1		10	20	ns
			Q2		25	40	
Q_g	Total Gate Charge	Q1 $V_{DS} = 15\text{ V}, I_D = 9.3\text{ A}, V_{GS} = 4.5\text{ V}$	Q1		17	27	nC
			Q2		13	21	
Q_{gs}	Gate-Source Charge		Q1		4		nC
			Q2		2.5		
Q_{gd}	Gate-Drain Charge	$V_{DS} = 15\text{ V}, I_D = -2.4\text{ A}, V_{GS} = -4.5\text{ V}$	Q1		5		nC
			Q2		2.0		

Drain-Source Diode Characteristics and Maximum Ratings

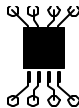
I_S	Maximum Continuous Drain-Source Diode Forward Current		Q1			2.1	A
			Q2			-2.1	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.1\text{ A}$ (Note 2)	Q1			1.2	V
		$V_{GS} = 0\text{ V}, I_S = -2.1\text{ A}$ (Note 2)	Q2			-1.2	

Notes:

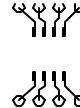
- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1 in^2 pad of 2 oz copper



b) 105°C/W when mounted on a 0.04 in^2 pad of 2 oz copper



c) 125°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width $< 300\ \mu\text{s}$, Duty Cycle $< 2.0\%$

Typical Characteristics: Q2

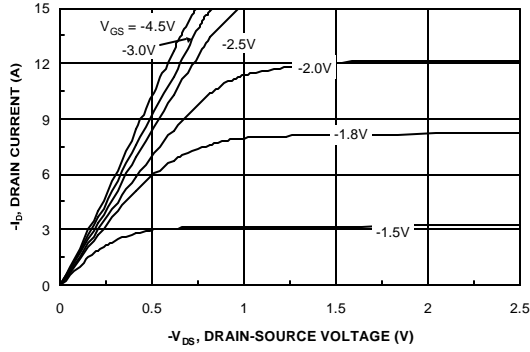


Figure 1. On-Region Characteristics.

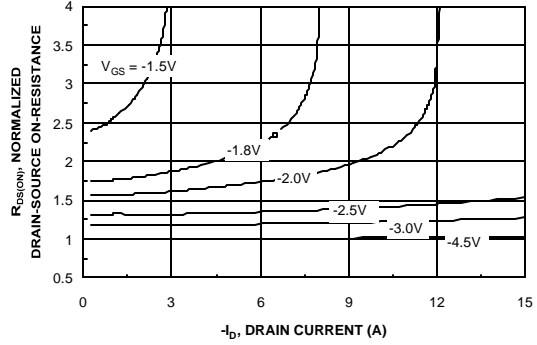


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

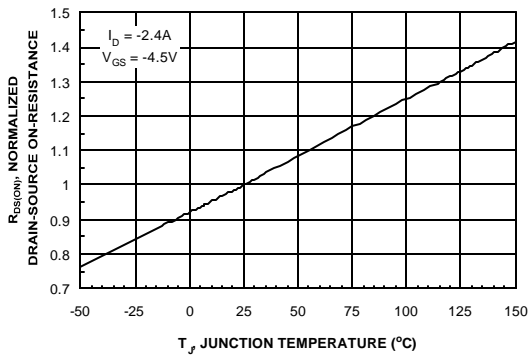


Figure 3. On-Resistance Variation with Temperature.

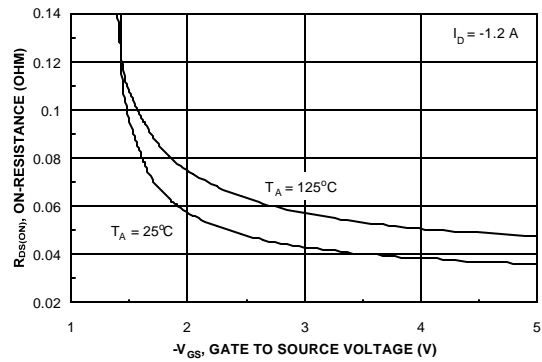


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

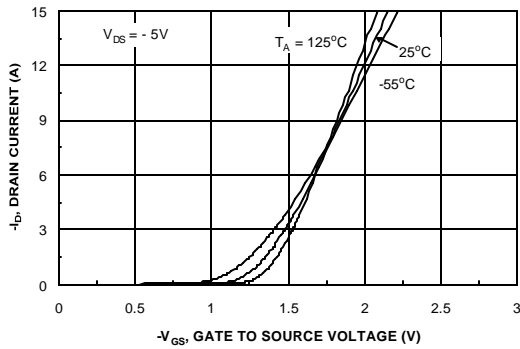


Figure 5. Transfer Characteristics.

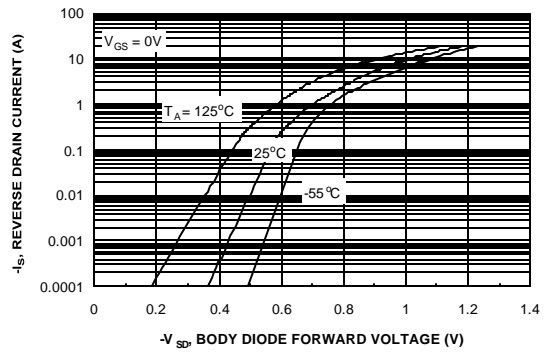


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics: Q2

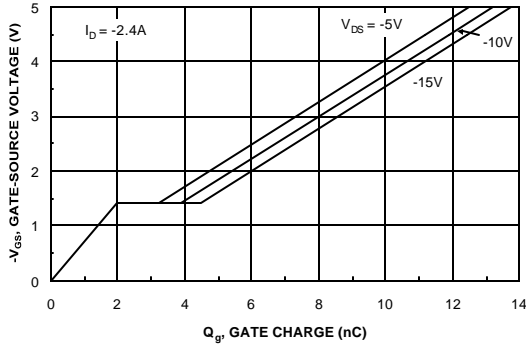


Figure 7. Gate Charge Characteristics.

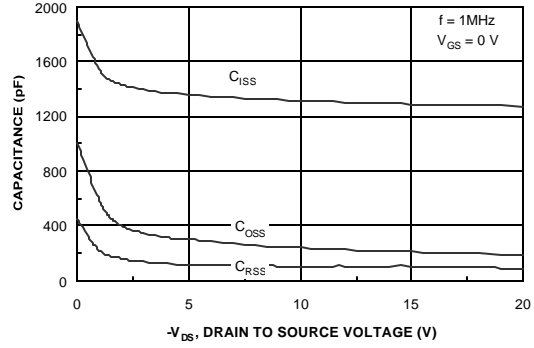


Figure 8. Capacitance Characteristics.

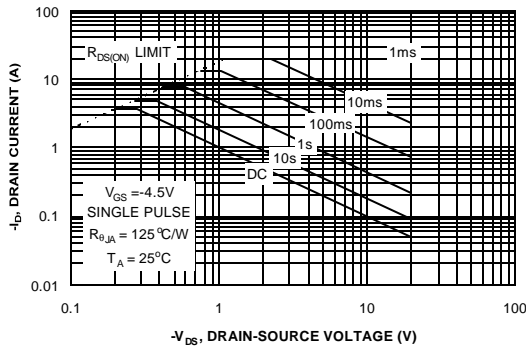


Figure 9. Maximum Safe Operating Area.

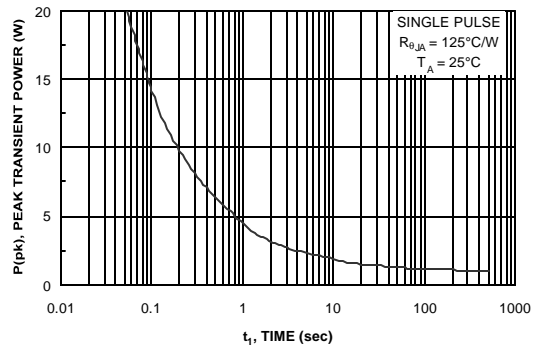


Figure 10. Single Pulse Maximum Power Dissipation.

Typical Characteristics: Q1

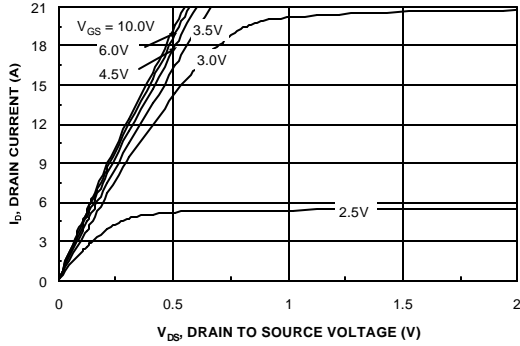


Figure 11. On-Region Characteristics.

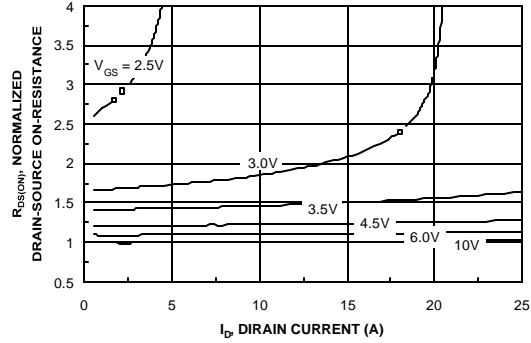


Figure 12. On-Resistance Variation with Drain Current and Gate Voltage.

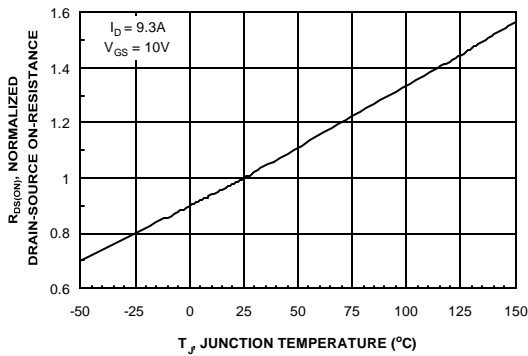


Figure 13. On-Resistance Variation with Temperature.

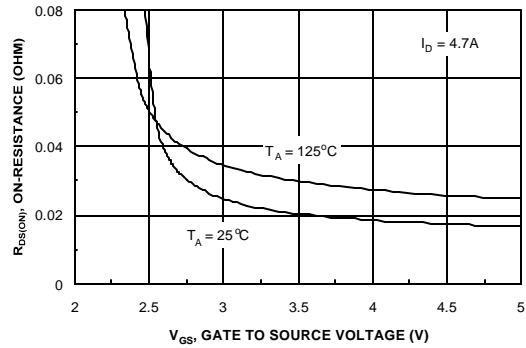


Figure 14. On-Resistance Variation with Gate-to-Source Voltage.

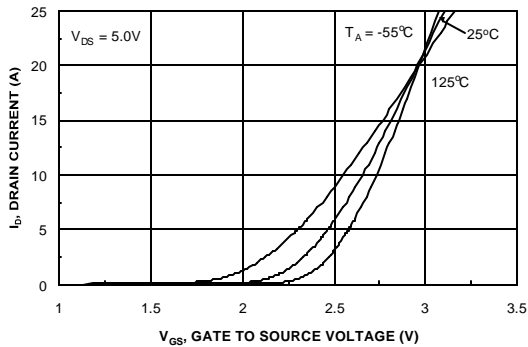


Figure 15. Transfer Characteristics.

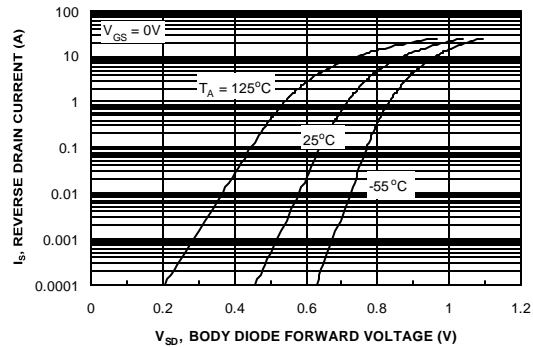


Figure 16. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics Q1

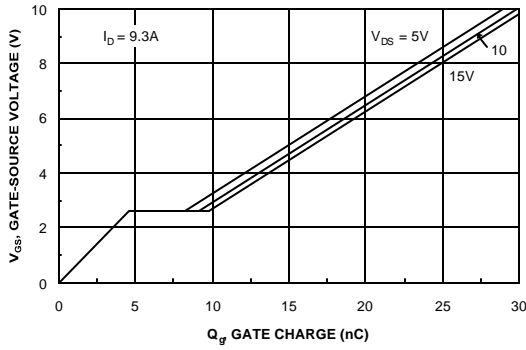


Figure 17. Gate Charge Characteristics.

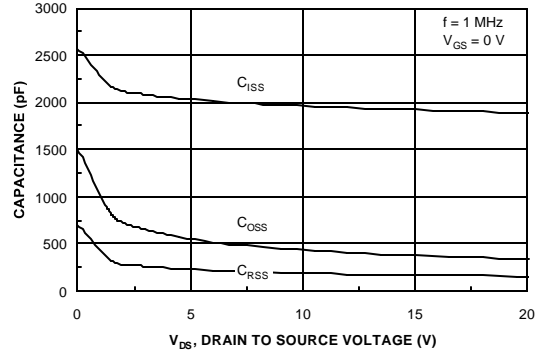


Figure 18. Capacitance Characteristics.

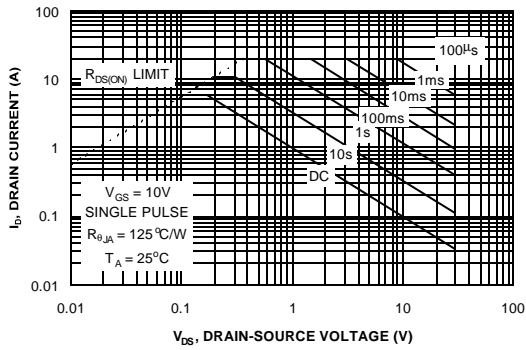


Figure 19. Maximum Safe Operating Area.

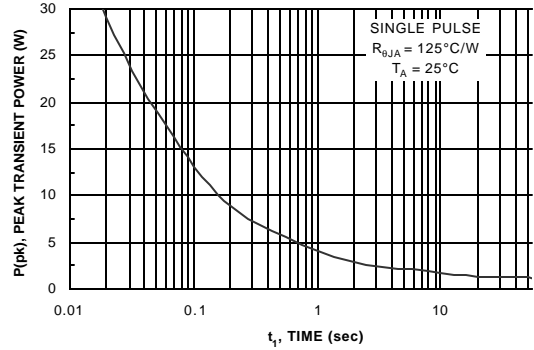


Figure 20. Single Pulse Maximum Power Dissipation.

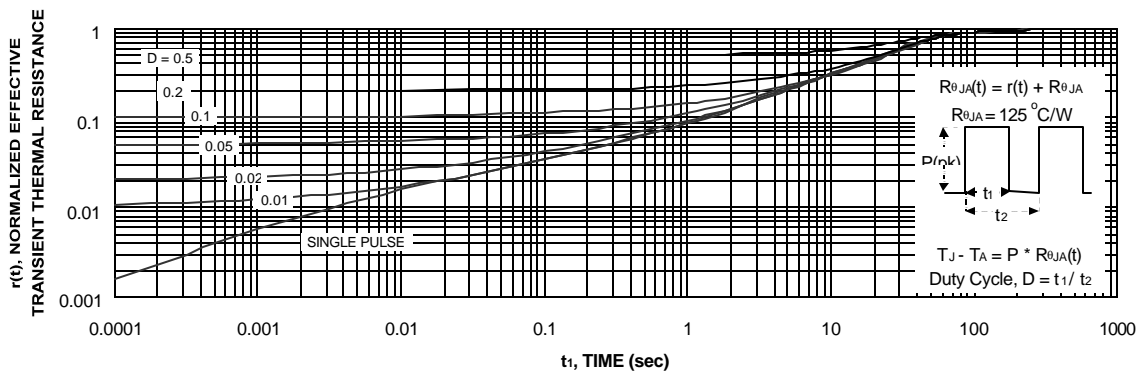


Figure 21. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

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DenseTrench TM	GTO TM	QFET TM	TinyLogic TM
DOMET TM	HiSeC TM	QS TM	UHC TM
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